

Trans MOSFET N-CH 60V 100A 3-Pin(2+Tab) D2PAK T/R

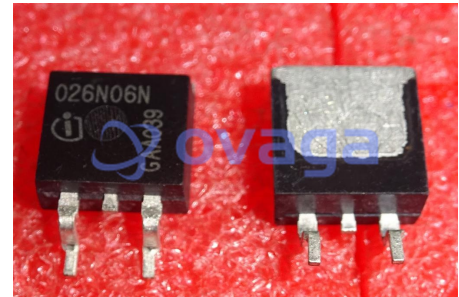
Manufacturers [Infineon Technologies Corporation](#)

Package/Case [OptiMOS5](#)

Product Type [Transistors](#)

RoHS

Lifecycle



Images are for reference only

Please submit RFQ for IPB026N06N or [Email to us: sales@ovaga.com](mailto:sales@ovaga.com) We will contact you in 12 hours.

[RFQ](#)

General Description

IPB026N06N is a specific type of power MOSFET (Metal Oxide Semiconductor Field-Effect Transistor) produced by Infineon Technologies. Here are some of its features:

Features

VDS (drain-source voltage) rating of 60V

ID (continuous drain current) rating of 100A

Low RDS(on) (drain-source on-resistance) of 2.6mΩ

TO-263 package

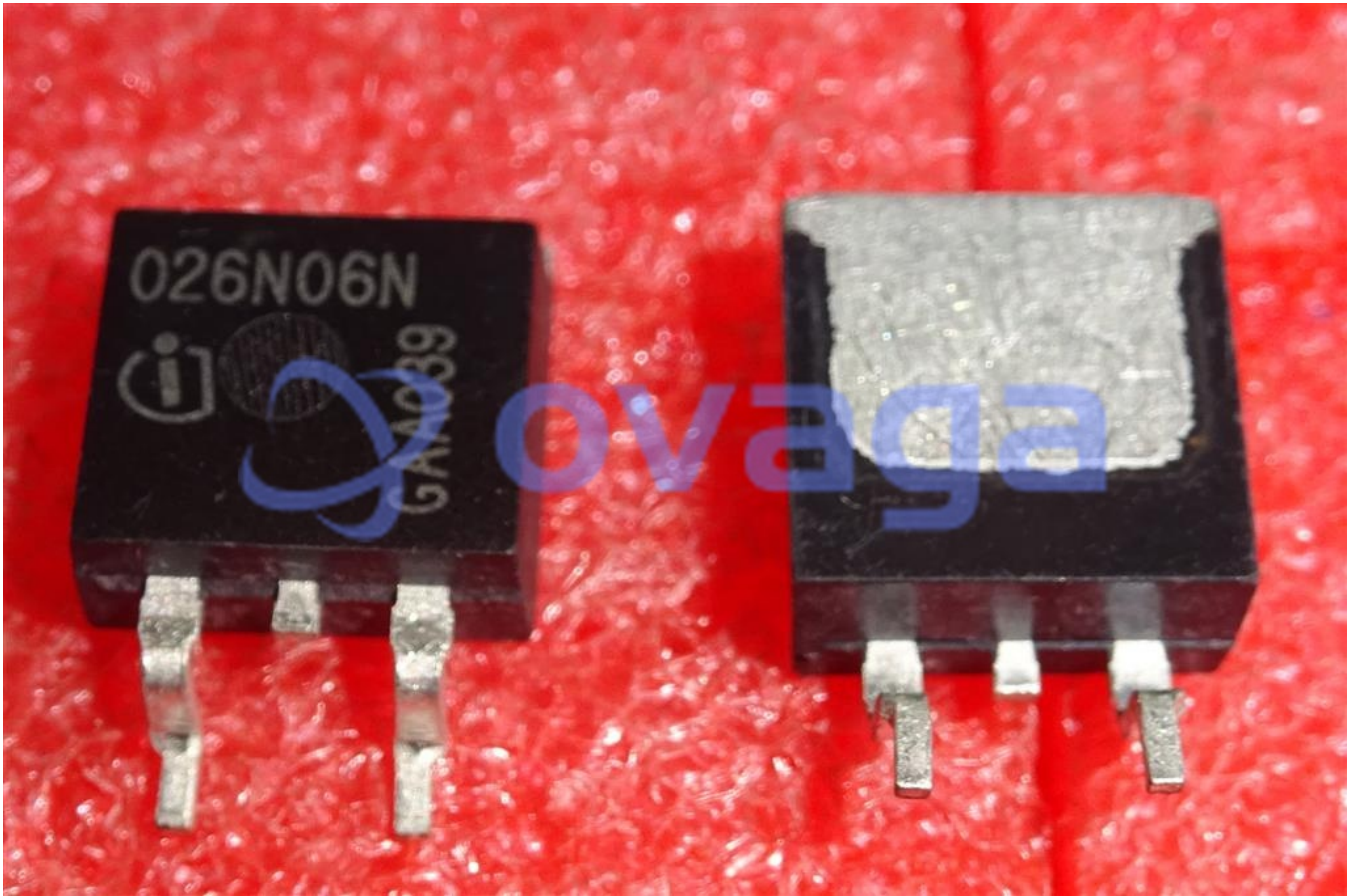
Application

Switching regulators

DC-DC converters

Motor control

Power supplies



Related Products



[IPP60R070CFD7](#)

Infineon Technologies Corporation
TO-220-3



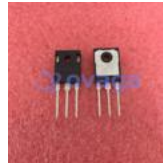
[IPB180N06S4-H1](#)

Infineon Technologies Corporation
PG-TO263-7-3



[IPG20N04S4-12](#)

Infineon Technologies Corporation
TDSON-8



[IPW65R080CFD](#)

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TO-247



[IPD25N06S4L-30](#)

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PG-TO252-3



[IPD180N10N3G](#)

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[IPP60R074C6](#)

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[IPD70R1K4P7S](#)

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